

# MMBT4401WT1G

## Switching Transistor

### NPN Silicon

#### Features

- Moisture Sensitivity Level: 1
- ESD Rating: Human Body Model; 4 kV,  
Machine Model; 400 V
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	40	Vdc
Collector - Base Voltage	$V_{CBO}$	60	Vdc
Emitter - Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	$I_C$	600	mAdc

#### THERMAL CHARACTERISTICS

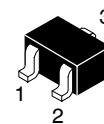
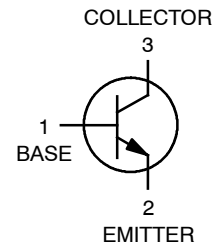
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



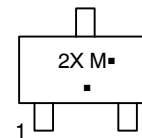
ON Semiconductor®

<http://onsemi.com>



SC-70 (SOT-323)  
CASE 419  
STYLE 3

#### MARKING DIAGRAM



(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT4401WT1G	SC-70 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector - Emitter Breakdown Voltage (Note 1) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	-	Vdc
Collector - Base Breakdown Voltage (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter - Base Breakdown Voltage (I <sub>E</sub> = 0.1 mA <sub>dc</sub> , I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	-	Vdc
Base Cutoff Current (V <sub>CE</sub> = 35 Vdc, V <sub>EB</sub> = 0.4 Vdc)	I <sub>BEV</sub>	-	0.1	μA <sub>dc</sub>

## ON CHARACTERISTICS (Note 1)

DC Current Gain (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 150 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 500 mA <sub>dc</sub> , V <sub>CE</sub> = 2.0 Vdc)	h <sub>FE</sub>	20 40 80 100 40	- - - 300 -	-
Collector - Emitter Saturation Voltage (I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B</sub> = 15 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )	V <sub>CE(sat)</sub>	- -	0.4 0.75	Vdc
Base - Emitter Saturation Voltage (I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B</sub> = 15 mA <sub>dc</sub> ) (I <sub>C</sub> = 500 mA <sub>dc</sub> , I <sub>B</sub> = 50 mA <sub>dc</sub> )	V <sub>BE(sat)</sub>	0.75 -	0.95 1.2	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 35 Vdc, V <sub>EB</sub> = 0.4 Vdc)	I <sub>CEx</sub>	-	0.1	μA <sub>dc</sub>

## SMALL-SIGNAL CHARACTERISTICS

Current - Gain - Bandwidth Product (I <sub>C</sub> = 20 mA <sub>dc</sub> , V <sub>CE</sub> = 10 Vdc, f = 100 MHz)	f <sub>T</sub>	250	-	MHz
Collector-Base Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>cb</sub>	-	6.5	pF
Emitter-Base Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>eb</sub>	-	30	pF
Input Impedance (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>ie</sub>	1.0	15	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>re</sub>	0.1	8.0	X 10 <sup>-4</sup>
Small - Signal Current Gain (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	40	500	-
Output Admittance (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	h <sub>oe</sub>	1.0	30	μmhos

## SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 30 Vdc, V <sub>EB</sub> = 2.0 Vdc, I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B1</sub> = 15 mA <sub>dc</sub> )	t <sub>d</sub>	-	15	ns
Rise Time		t <sub>r</sub>	-	20	
Storage Time	(V <sub>CC</sub> = 30 Vdc, I <sub>C</sub> = 150 mA <sub>dc</sub> , I <sub>B1</sub> = I <sub>B2</sub> = 15 mA <sub>dc</sub> )	t <sub>s</sub>	-	225	ns
Fall Time		t <sub>f</sub>	-	30	

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

## SWITCHING TIME EQUIVALENT TEST CIRCUITS

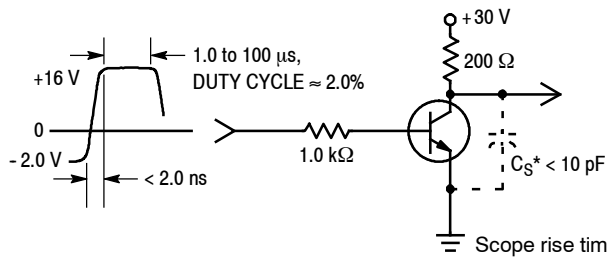


Figure 1. Turn-On Time

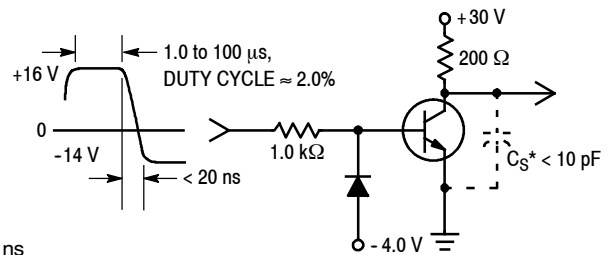


Figure 2. Turn-Off Time

# MMBT4401WT1G

## TRANSIENT CHARACTERISTICS

— 25°C    - - - 100°C

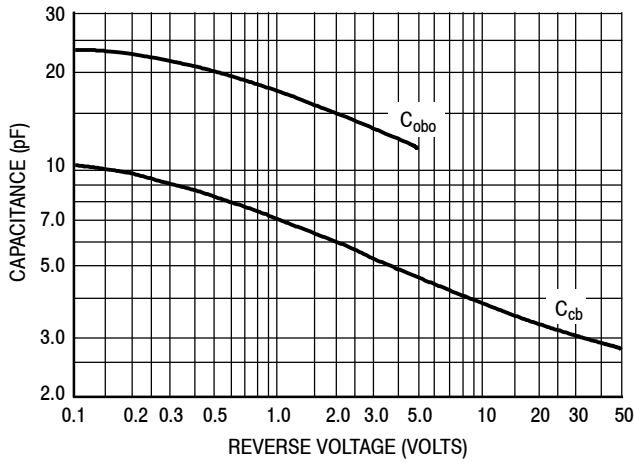


Figure 3. Capacitances

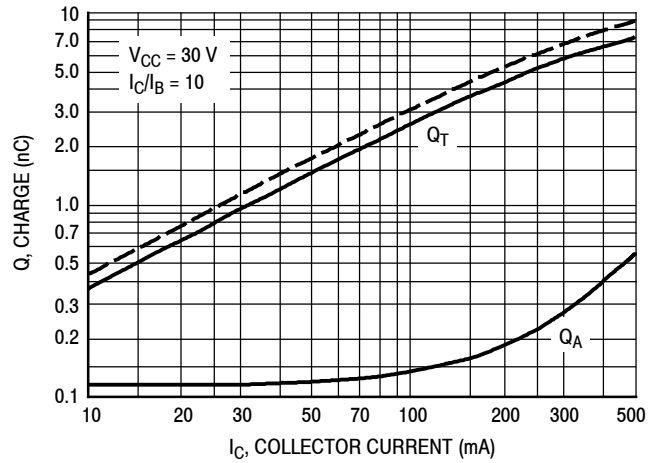


Figure 4. Charge Data

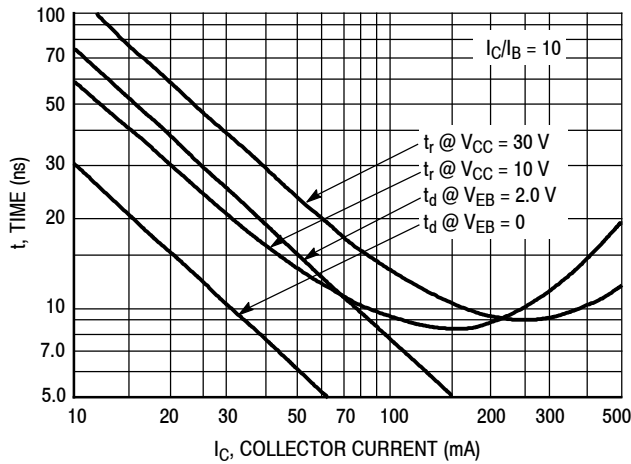


Figure 5. Turn-On Time

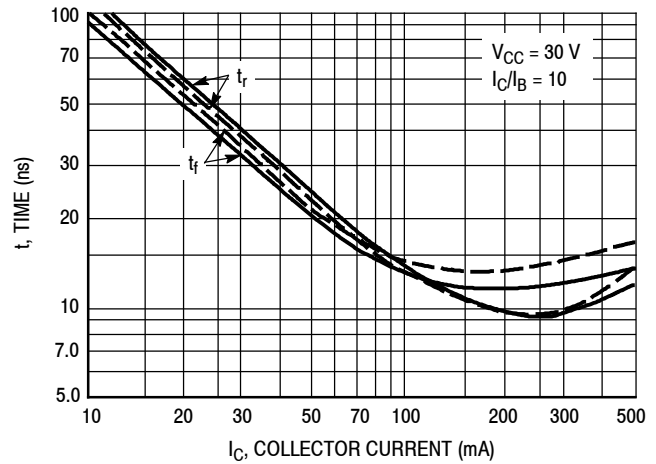


Figure 6. Rise and Fall Times

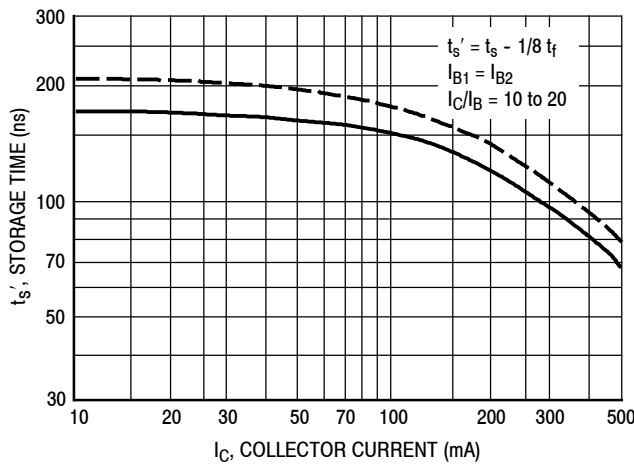


Figure 7. Storage Time

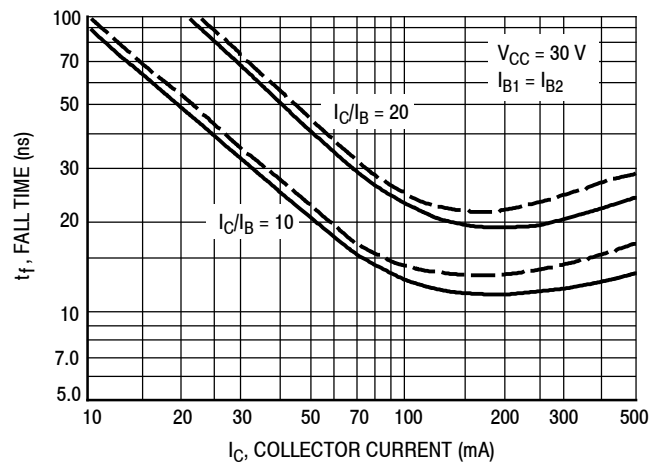


Figure 8. Fall Time

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## SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ ; Bandwidth = 1.0 Hz

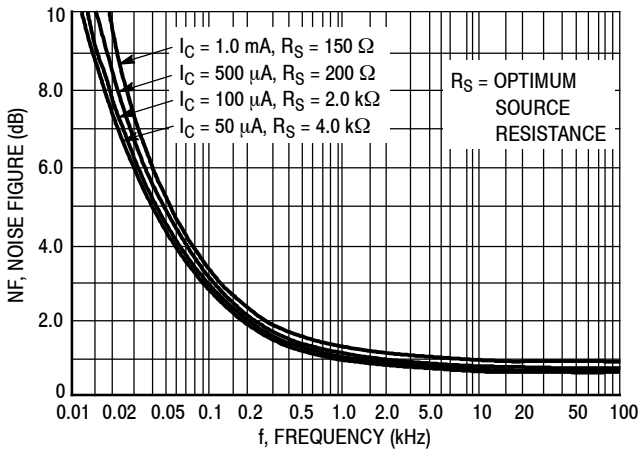


Figure 9. Frequency Effects

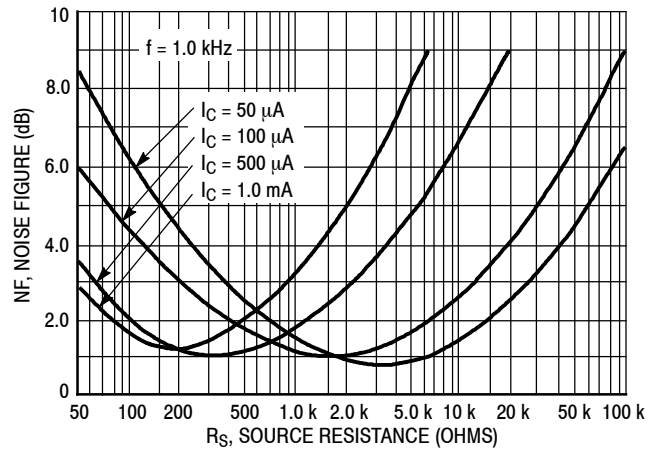


Figure 10. Source Resistance Effects

## h PARAMETERS

$V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$

This group of graphs illustrates the relationship between  $h_{fe}$  and other “h” parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4401WT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

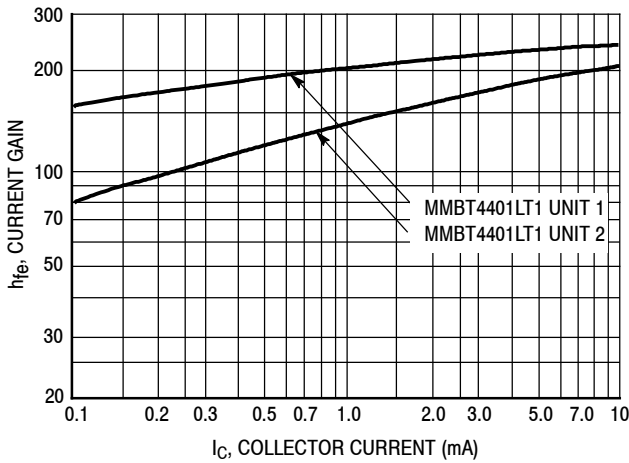


Figure 11. Current Gain

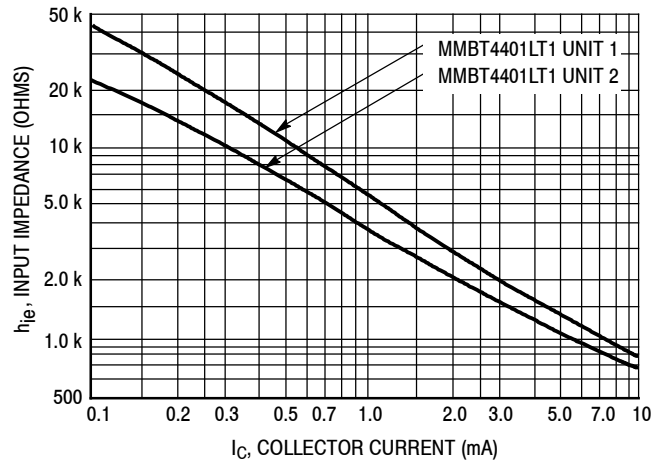


Figure 12. Input Impedance

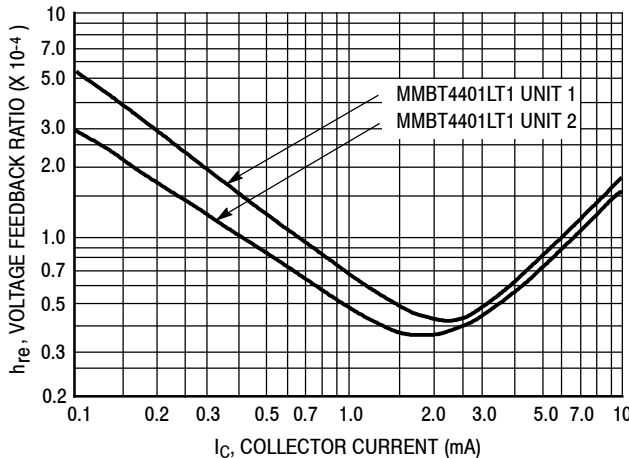


Figure 13. Voltage Feedback Ratio

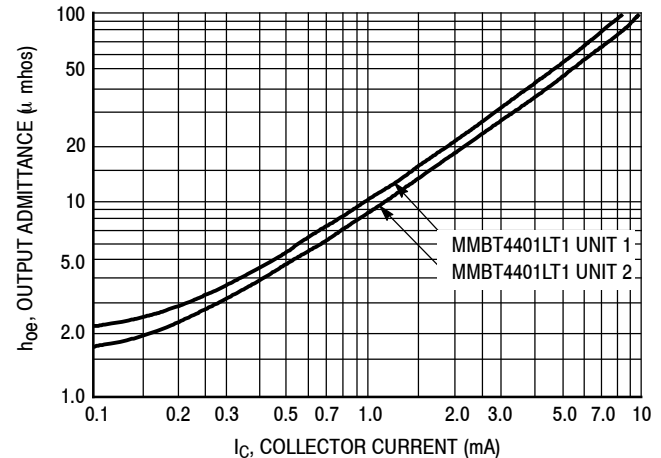


Figure 14. Output Admittance

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## STATIC CHARACTERISTICS

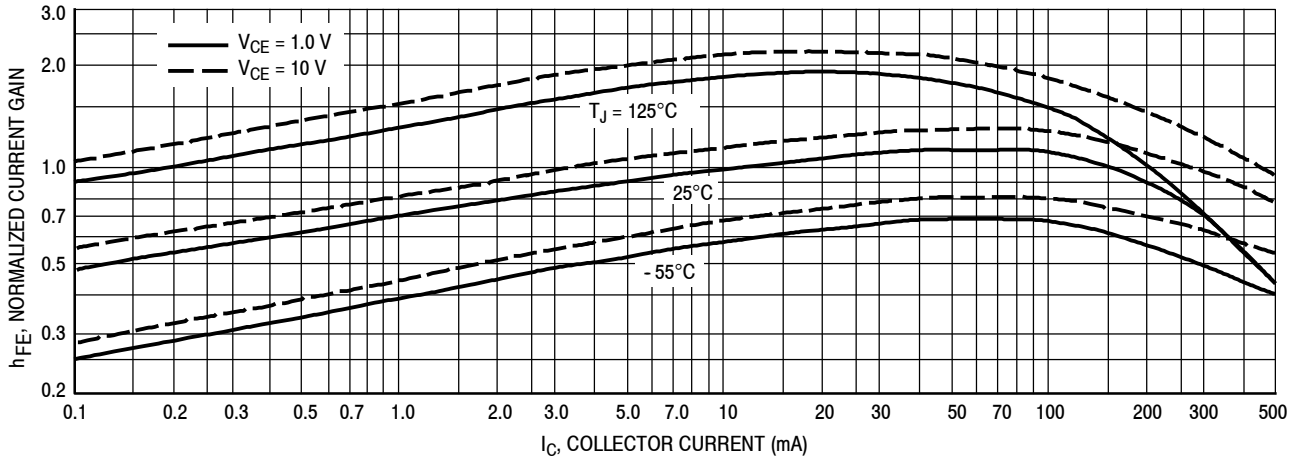


Figure 15. DC Current Gain

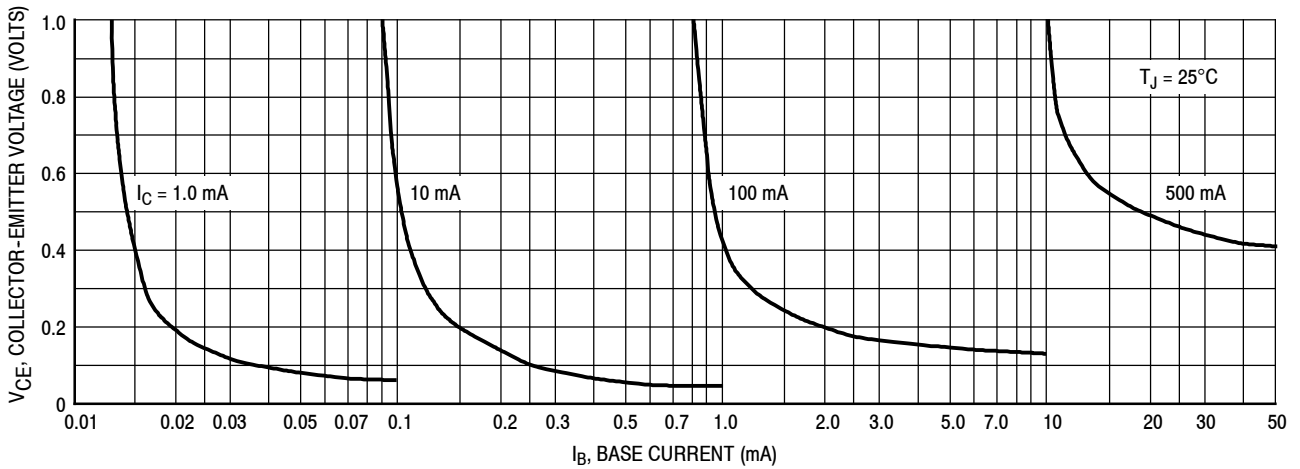


Figure 16. Collector Saturation Region

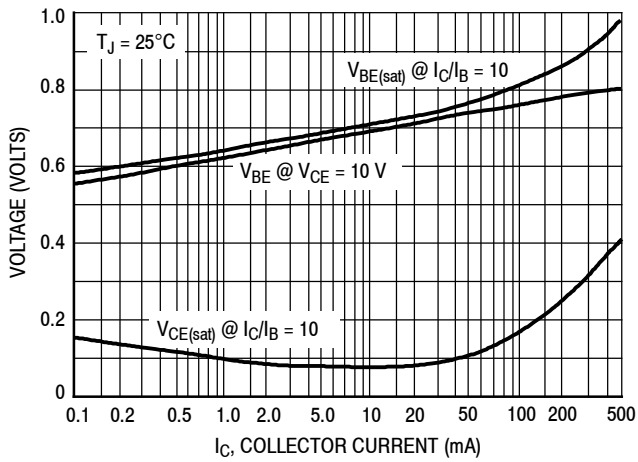


Figure 17. "On" Voltages

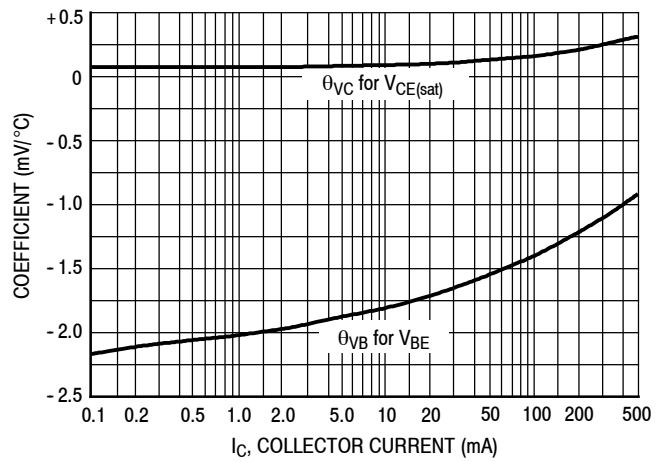
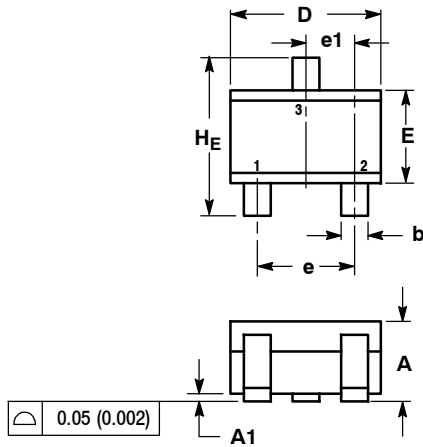


Figure 18. Temperature Coefficients

# MMBT4401WT1G

## PACKAGE DIMENSIONS

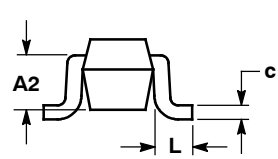
SC-70 (SOT-323)  
CASE 419-04  
ISSUE N



NOTES:

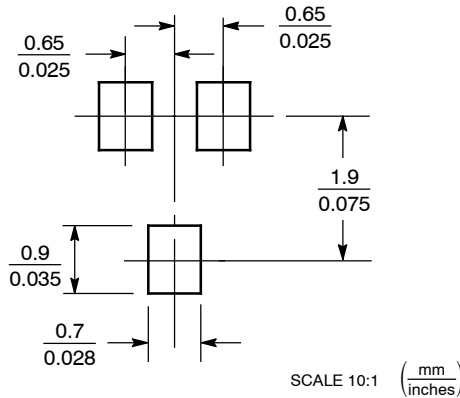
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



STYLE 3:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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